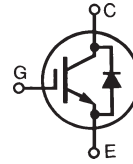


HiPerFAST™ IGBT IXGH15N120B2D1 IXGT15N120B2D1

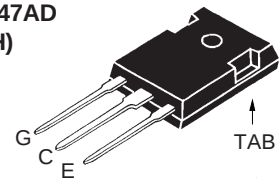
Optimized for 10-20 KHz hard switching and up to 100 KHz resonant switching



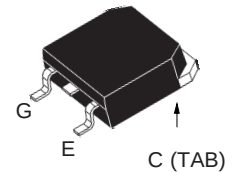
V_{CES}	= 1200	V
I_{C25}	= 30	A
$V_{CE(sat)}$	= 3.3	V
$t_{fi(typ)}$	= 137	ns

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	30	A
I_{C90}	$T_C = 90^\circ\text{C}$	15	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	60	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10\ \Omega$ Clamped inductive load	$I_{CM} = 40$ @ $0.8\ V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	192	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10 Nm/lb.in.	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Maximum tab temperature soldering SMD devices for 10s		260	$^\circ\text{C}$
Weight	TO-247AD / TO-268	6 / 4	g

TO-247AD
(IXGH)



TO-268
(IXGT)



G = Gate
E = Emitter

C = Collector
TAB = Collector

Features

- International standard packages: JEDEC TO-247AD & TO-268
- IGBT and anti-parallel FRED in one package
- MOS Gate turn-on
 - drive simplicity
- Fast Recovery Exptaxial Diode (FRED)
 - soft recovery with low I_{RM}

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Saves space (two devices in one package)
- Easy to mount with 1 screw (isolated mounting screw hole)
- Reduces assembly time and cost

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\ \mu\text{A}$, $V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = V_{CES}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		100 μA
	$V_{GE} = 0\text{ V}$			3.5 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{CE90}$, $V_{GE} = 15$	$T_J = 125^\circ\text{C}$	2.7	3.3 V
				V

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10 V$, Pulse test, $t \leq 300 \mu s$, duty cycle $\leq 2 \%$	12	15	S
C_{ies}	$V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz$		1700	pF
C_{oes}			95	pF
C_{res}			38	pF
Q_g	$I_C = I_{C90}, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}$		86	nC
Q_{ge}			13	nC
Q_{gc}			26	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ C$ $I_C = I_{C90}, V_{GE} = 15 V$ $V_{CE} = 960 V, R_G = R_{off} = 10 \Omega$ Remarks: Switching times may increase for $V_{CE} (Clamp) > 0.8 V_{CES}$, higher T_J or increased R_G		25	ns
t_{ri}			15	ns
$t_{d(off)}$			165	ns
t_{fi}			137	ns
E_{off}			1.4	2.3 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ C$ $I_C = I_{C90}, V_{GE} = 15 V$ $V_{CE} = 960 V, R_G = R_{off} = 10 \Omega$ Remarks: Switching times may increase for $V_{CE} (Clamp) > 0.8 V_{CES}$, higher T_J or increased R_G		25	ns
t_{ri}			18	ns
E_{on}			0.60	mJ
$t_{d(off)}$			260	ns
t_{fi}			305	ns
E_{off}			2.8	mJ
R_{thJC}	TO-247			0.65 K/W
R_{thCK}			0.25	K/W

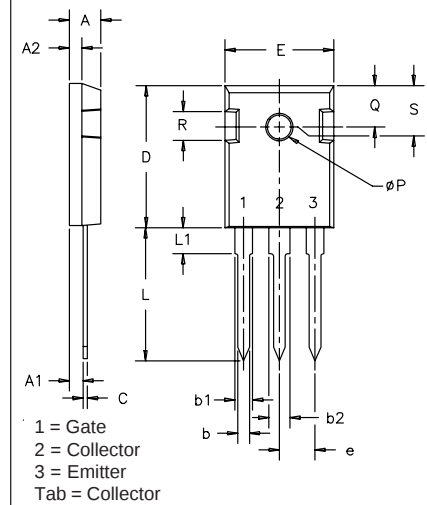
Reverse Diode (FRED)

Characteristic Values

($T_J = 25^\circ C$, unless otherwise specified)

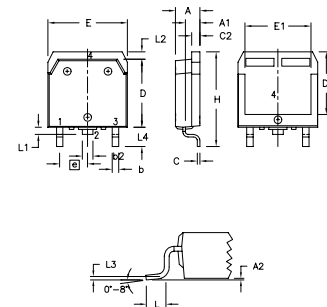
Symbol	Test Conditions	min.	typ.	max.
I_F	$T_C = 100^\circ C$			15 A
V_F	$I_F = 15 A, V_{GE} = 0 V$ $I_F = 15 A, V_{GE} = 0 V, T_J = 125^\circ C$		2.1	2.8 V
I_{RM}	$I_F = 25 A; -di_F/dt = 100 A/\mu s, V_R = 100 V$		6	A
t_{rr}	$V_{GE} = 0 V, T_J = 100^\circ C$		165	ns
R_{thJC}				1.6 K/W

TO-247 AD Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A1	.087	.102	2.2	2.54
A2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b1	.065	.084	1.65	2.13
b2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
ØP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

TO-268 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A1	2.7	2.9	.106	.114
A2	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b2	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E1	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344